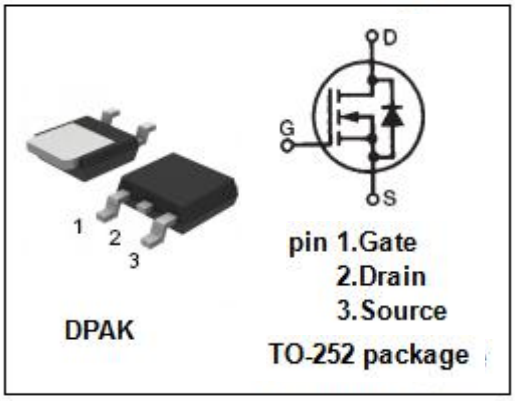
iscN-Channel MOSFET Transistor IRFR1N60A

• FEATURES

- Low drain-source on-resistance:
  R_{DS}(ON) =7Ω (MAX)
- Enhancement mode:
  Vth = 2.0 to 4.0V (V_{DS} = 10 V, I_D=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

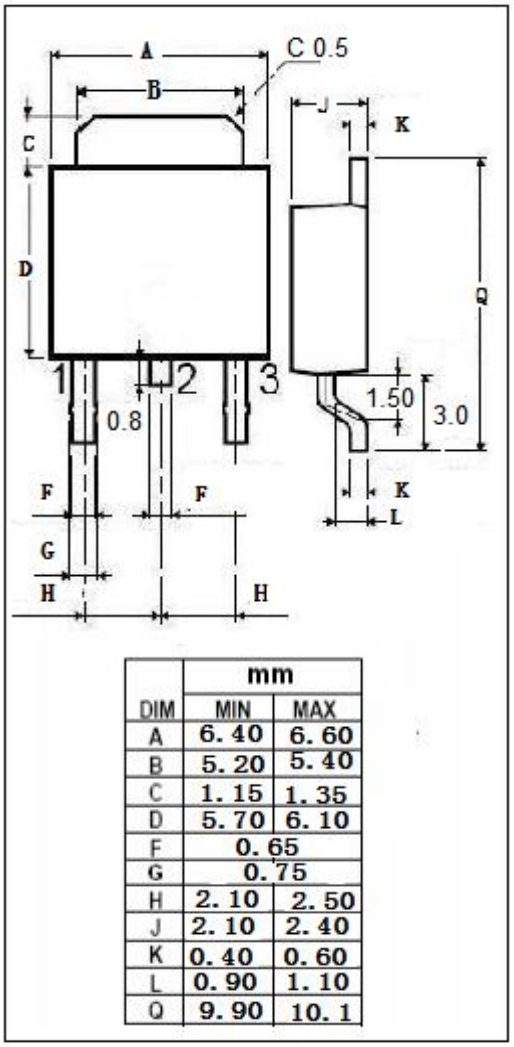


• DESCRITION

- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous	1.4	A
I_{DM}	Drain Current-Single Pulsed	5.6	A
P_D	Total Dissipation @T_C=25℃	36	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=0.25mA	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D=0.84A			7	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V; V_{GS}= 0V V_{DS}=480V; V_{GS}= 0V;T_J=125℃			25 250	uA
V_{SDF}	Diode forward voltage	I_{DR} =1.4A, V_{GS} = 0 V			1.6	V